

## Product Summary

$BV_{DSS}$	$R_{DS(ON)} \text{ Max}$	$I_D \text{ Max}$ $T_c = +25^\circ\text{C}$
60V	10mΩ @ $V_{GS} = 10\text{V}$	57A
	12.8mΩ @ $V_{GS} = 4.5\text{V}$	51A

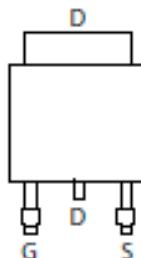
## Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high- efficiency power management applications.

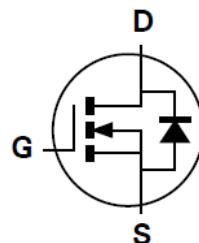
- Power Management Functions
- DC-DC Converters
- Backlighting



Top View



Pin Out Top View



Equivalent Circuit

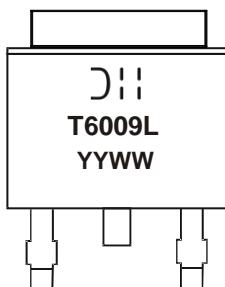
## Ordering Information (Note 4)

Part Number	Case	Packaging
DMT6009LK3-13	TO252	2,500/Tape & Reel

Notes:

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



DII = Manufacturer's Marking  
T6009L = Product Type Marking Code  
YYWW = Date Code Marking  
YY = Last Two Digits of Year (ex: 15 = 2015)  
WW = Week Code (01 to 53)

**Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	$V_{DSS}$	60	V	
Gate-Source Voltage	$V_{GSS}$	$\pm 16$	V	
Continuous Drain Current (Note 5) $V_{GS} = 10\text{V}$	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	$I_D$	13.3 10.6	A
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	$T_C = +25^\circ\text{C}$ $T_C = +70^\circ\text{C}$	$I_D$	57 46	A
Maximum Continuous Body Diode Forward Current (Note 6)	$I_S$	80	A	
Pulsed Drain Current (10 $\mu\text{s}$ Pulse, Duty Cycle = 1%)	$I_{DM}$	90	A	
Avalanche Current, $L=0.1\text{mH}$	$I_{AS}$	20.3	A	
Avalanche Energy, $L=0.1\text{mH}$	$E_{AS}$	20.6	$\text{mJ}$	

**Thermal Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$P_D$	2.6	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	47	$^\circ\text{C}/\text{W}$
Total Power Dissipation (Note 6)	$P_D$	50	W
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	2.5	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	60	-	-	V	$V_{GS} = 0\text{V}, I_D = 1\text{mA}$
Zero Gate Voltage Drain Current	$I_{DSS}$	-	-	1	$\mu\text{A}$	$V_{DS} = 48\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	$I_{GSS}$	-	-	$\pm 100$	nA	$V_{GS} = \pm 16\text{V}, V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	$V_{GS(\text{TH})}$	0.7	1.4	2	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(\text{ON})}$	-	8.3	10	$\text{m}\Omega$	$V_{GS} = 10\text{V}, I_D = 13.5\text{A}$
		-	9.6	12.8	$\text{m}\Omega$	$V_{GS} = 4.5\text{V}, I_D = 11.5\text{A}$
Diode Forward Voltage	$V_{SD}$	-	0.9	1.2	V	$V_{GS} = 0\text{V}, I_S = 20\text{A}$
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	$C_{iss}$	-	1,925	-	pF	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Output Capacitance	$C_{oss}$	-	438	-		
Reverse Transfer Capacitance	$C_{rss}$	-	41	-	nC	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Gate Resistance	$R_g$	-	1.7	-		
Total Gate Charge ( $V_{GS} = 4.5\text{V}$ )	$Q_g$	-	15.6	-	ns	$V_{DS} = 30\text{V}, I_D = 13.5\text{A}$
Total Gate Charge ( $V_{GS} = 10\text{V}$ )	$Q_g$	-	33.5	-		
Gate-Source Charge	$Q_{gs}$	-	4.7	-	ns	$V_{DD} = 30\text{V}, V_{GS} = 10\text{V}, R_G = 6\Omega, I_D = 13.5\text{A}$
Gate-Drain Charge	$Q_{gd}$	-	5.3	-		
Turn-On Delay Time	$t_{D(\text{ON})}$	-	4.5	-	ns	$V_{DD} = 30\text{V}, V_{GS} = 10\text{V}, R_G = 6\Omega, I_D = 13.5\text{A}$
Turn-On Rise Time	$t_R$	-	8.6	-		
Turn-Off Delay Time	$t_{D(\text{OFF})}$	-	35.9	-	ns	$I_F = 13.5\text{A}, dI/dt = 400\text{A}/\mu\text{s}$
Turn-Off Fall Time	$t_F$	-	15.7	-		
Body Diode Reverse Recovery Time	$t_{RR}$	-	18.2	-	ns	$I_F = 13.5\text{A}, dI/dt = 400\text{A}/\mu\text{s}$
Body Diode Reverse Recovery Charge	$Q_{RR}$	-	33.1	-		

Notes:

5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
6. Device mounted on infinite heat sink and measured by thermal couple attached on bottom heat sink of package.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

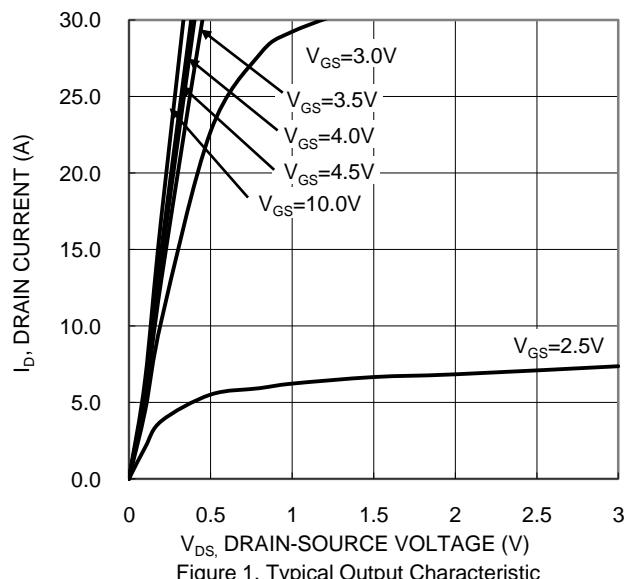


Figure 1. Typical Output Characteristic

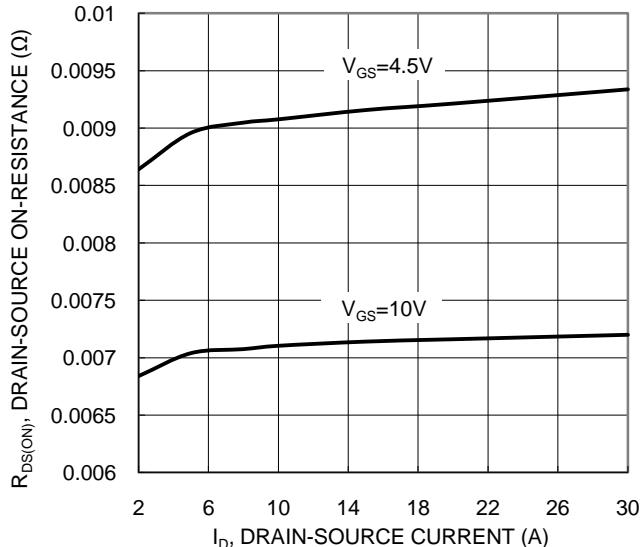


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

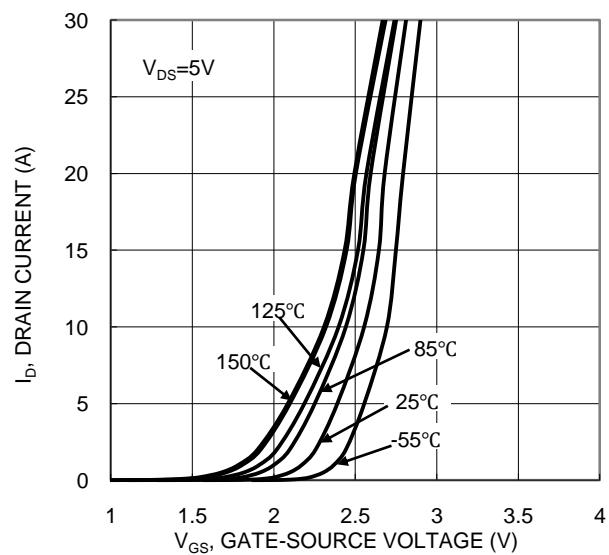


Figure 2. Typical Transfer Characteristic

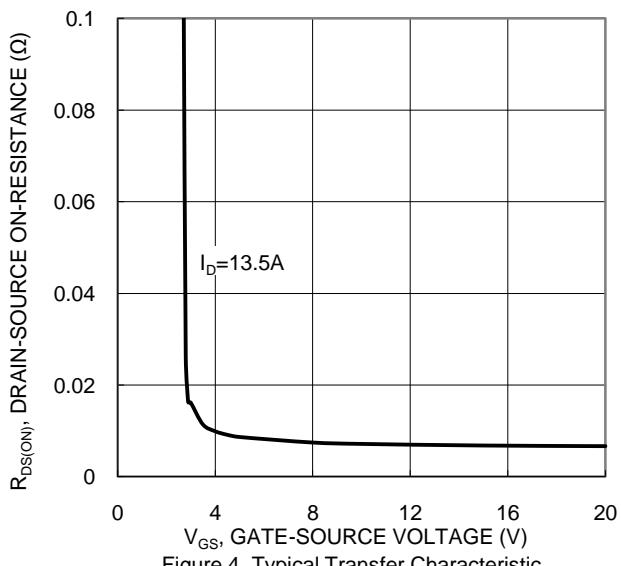


Figure 4. Typical Transfer Characteristic

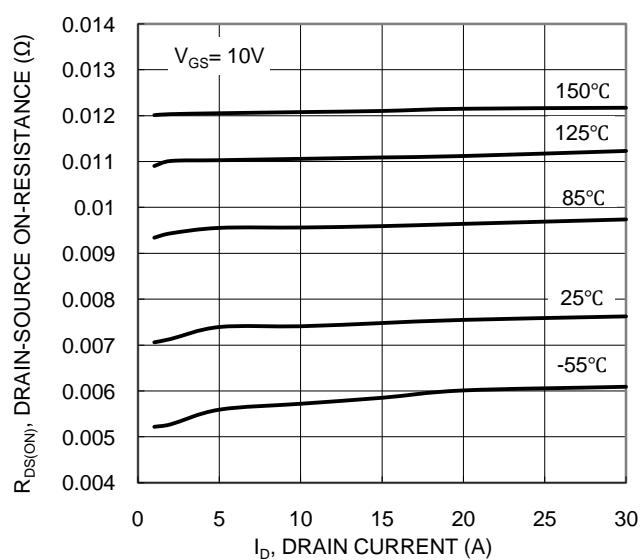


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

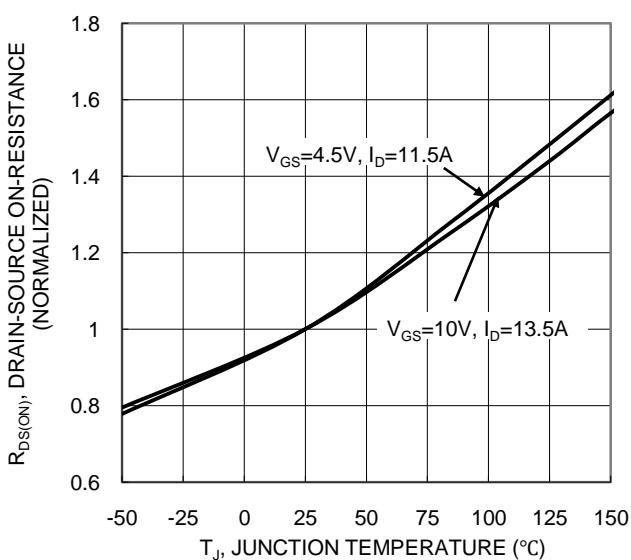


Figure 6. On-Resistance Variation with Junction Temperature

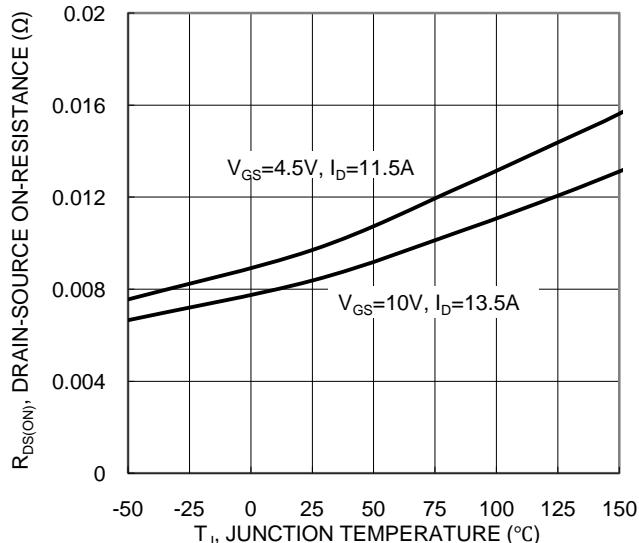


Figure 7. On-Resistance Variation with Junction Temperature

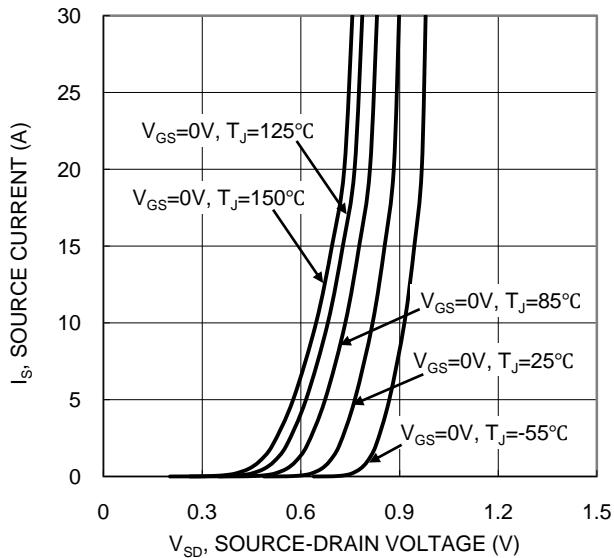


Figure 9. Diode Forward Voltage vs. Current

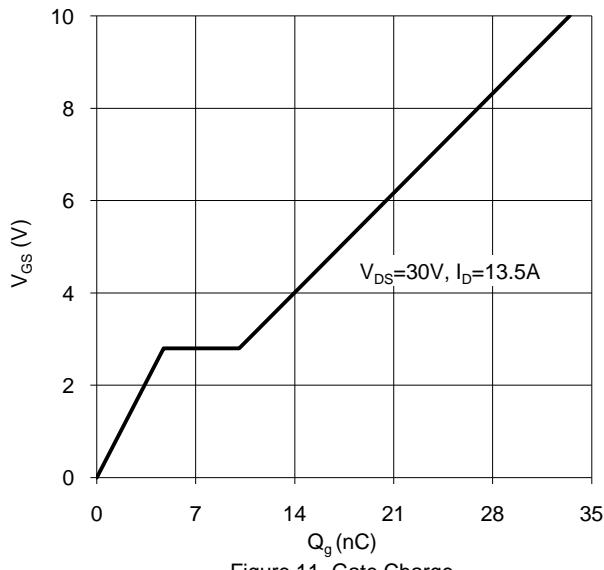


Figure 11. Gate Charge

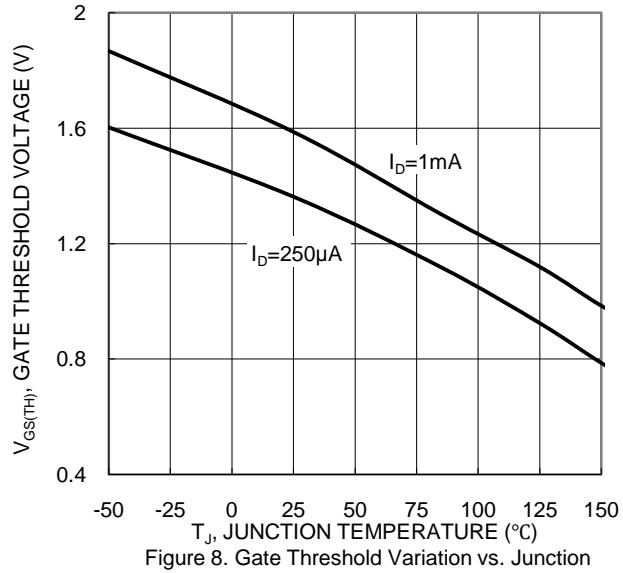


Figure 8. Gate Threshold Variation vs. Junction Temperature

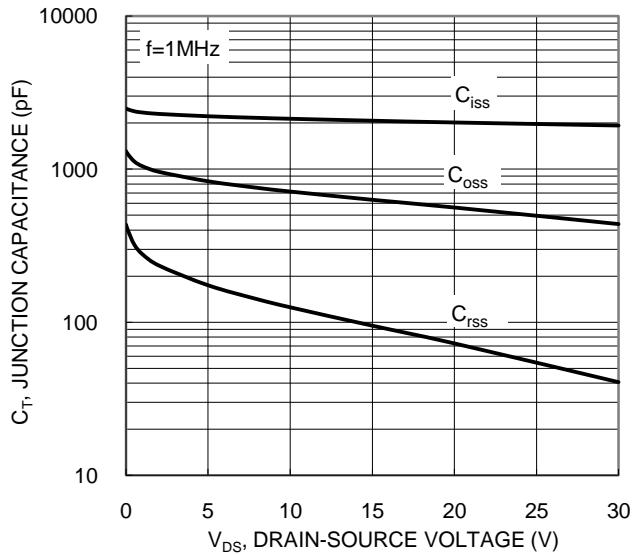


Figure 10. Typical Junction Capacitance

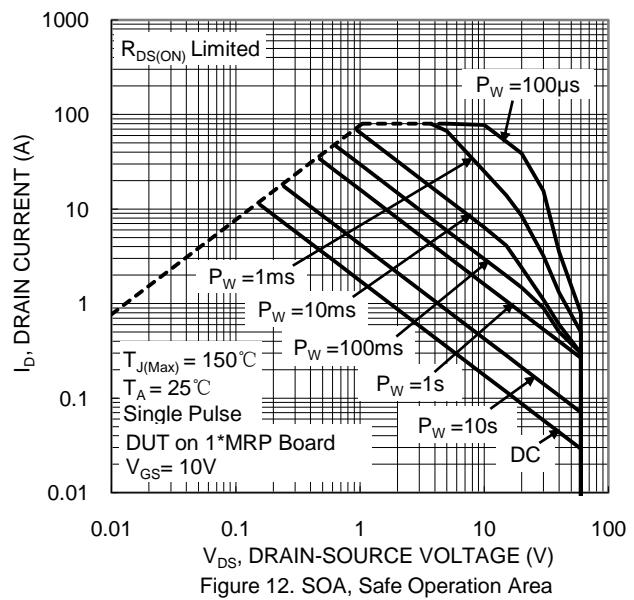


Figure 12. SOA, Safe Operation Area

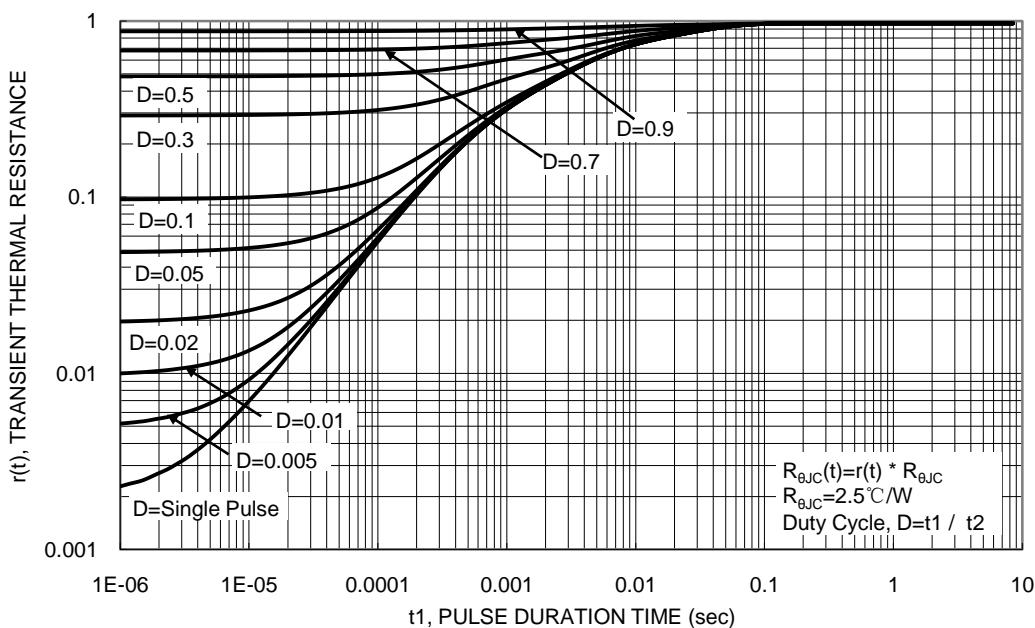
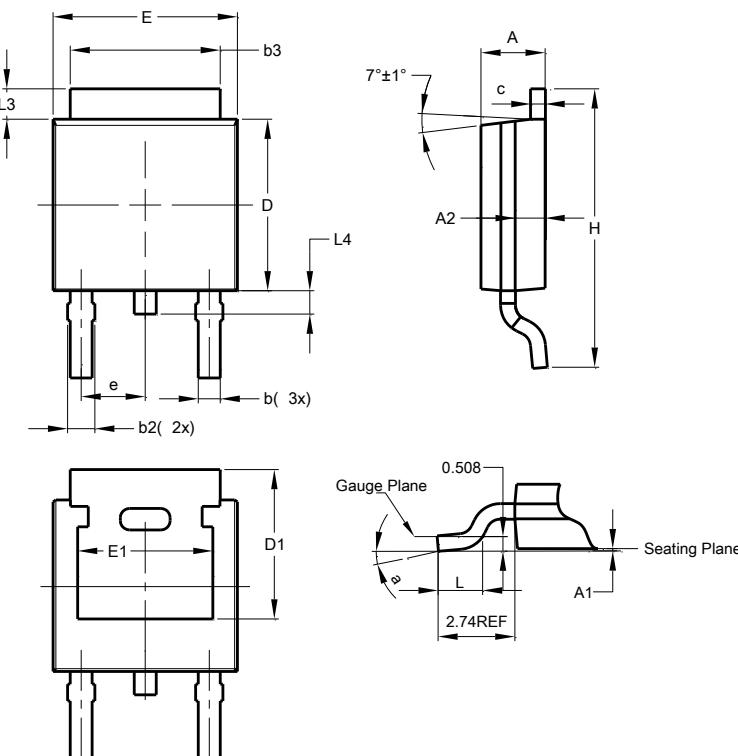


Figure 13. Transient Thermal Resistance

## Package Outline Dimensions

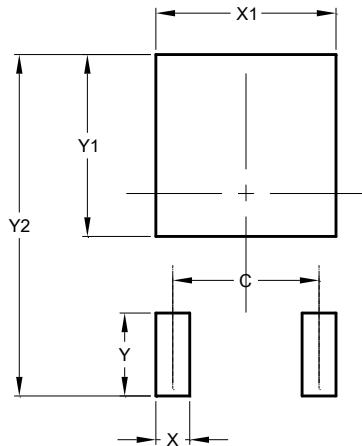
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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